As a below-named inventor, I hereby declare that this declaration is for the national phase of the PCT

My residence, post office address and ci the subject matter which is claimed and	for which a patent is sought on the	e invention entitled NITRIDS	SEMICONDUCTOR DEVI
AND MANUFACTURING METIK international Application No the contents of the above identified spec tury to disclose information which is ma Regulations, Section 1 56(a)	filed on	amended by any amendment referre	have reviewed and understanded to above. I acknowledge the
hereby claim foreign priority benefits userificate or any PCT International application dentified below any foreign application country other than the United States filed priority is claimed	ication(s) designating at least one- for patent or inventor's certificate	country other than the United States or any PCT International application	s listed below and have also on(s) designating at least one
Princ Foreign Application(s)			Priority Claim
Prior Foreign Application(s)			Yes No
P 11 - 030990	Japan	09/02/1999	X
Number	Country	Day/Monto/Year Filed	
P 11-331797	Japan	2 <u>2/11/1999</u>	x
Number	Country	Day/Month/Year Filed	
Application Serial No	Filing Date	Status Pa	itented, Pending, Abandoned
hereby declare that all statements made theved to be true; and further that these unishable by fine or imprisonment or but ay jeopardize the validity of the applica	herein of my own knowledge are statements were made with the ki th, under Section 1001 of Title 18	true and that all statements made o nowledge that willful false statemen	n information and belief are ts and the like so made are
Ill Name of First Joint Inventor Sh	inichi NAGAHAMA	1	
×	k . i \wedge	Mary Nun	
ventor's Signature	Men	ingo va	December 24, 1999
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st Office Address C/O Nichi	a Corporation, 491- 774-8601 JAPAN	100, Oka, Kaminakach	no, Anan-shi,
II Name of Second Joint Inventor:	huji NAKAMURA		
ventor's Signature:	Mellen		December 24, 1999
sidence Anan-shi, Tokush	nima, Japan		Date
tizenship. <u>Japan</u> st Office Address <u>C/O NiChia</u>	Corporation, 491-1	00. Oka. Kaminakacho	o. Anan-shi
	774-8601 JAPAN	ov via nammanacik	W WIGHT SHITE





IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Shinichi NAGAHAMA et al. Serial No.: Filed:) Group) Art Unit:) Examiner:)))) POWER OF ATTORNEY BY ASSIGNEE
For: NITRIDE SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF)))
Assistant Commissioner for Patents Washington, D.C. 20231	
Sir:	
Nichia Corporation	, Assignee of the above-identified
application by Assignment dated 24/12/1999 he	ereby appoints the members of the firm of
HAVERSTOCK & OWENS LLP, a firm including Th	omas B. Haverstock (Reg. No. 32,571) and Jonathan O.
Owens (Reg. No. 37,902) 260 Sheridan Avenue, Suite	420, Palo Alto, California 94306, telephone: (650) 833-
0160, facsimile: (650) 833-0170, as its attorneys with	full power of substitution to prosecute this application and
to transact all business in the Patent and Trademark Of	ffice in connection therewith.
Please direct all correspondence regarding this	application to the following:
Thomas B. Haverstock HAVERSTOCK & OWENS LLP 260 Sheridan Avenue, Suite 420 Palo Alto, California 94306 Telephone: (650) 833-0160 Facsimile: (650) 833-0170	
I hereby certify that the Assignment document	t filed with the application or filed subsequent to the filing
date of the application, has been reviewed and I hereby	certify that, to the best of my knowledge and belief, title
is with	·
	eme: Eiji OCAWA President